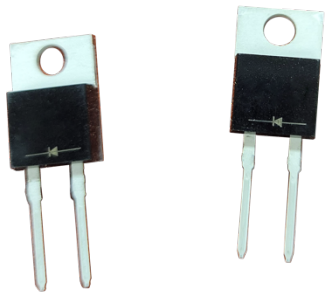
HPD SERIES

1.6 to 2.2kV, 10A, 75nS to Standard Recovery
High Power Rectifiers



Features

- Standard and Fast Recovery High Power Silicon Rectifiers – 10 Amps
- TO-220 Industry Standard Package

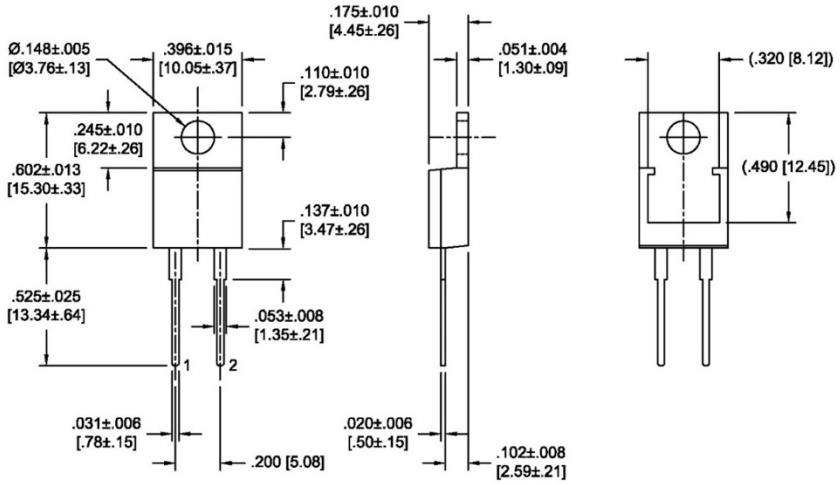
Specifications

Part Number	Values							
	V_{RRM} Maximum Repetitive Reverse Voltage (V)	I_{FAVM} Maximum Average Forward Current (A) *At T_A = 55°C*	V_F Maximum Forward Voltage Drop (V) *At I_{FAVM}*	I_R Maximum Leakage Current (µA) *At V_{RRM}*	I_{FSM} Maximum Surge Current (A) *At 8.3 mS, Single Half Sine*	T_{RR} Maximum Reverse Recovery Time (nS) *I_F = 0.5A; I_R = -1.0A; I_{RR} = -0.25A*	C_J Typical Junction Capacitance (pF) *At V_R = 0VDC, f = 1MHz*	$R_{\theta JC}$ Typical Thermal Resistance (°C/W) *Junction to Case, Mounted to 1.65" x 2.5" Multi-Fin Heatsink*
HPD1600	1600	10	3.4	5	100	-	40	1.1
HPD1600F	1600	10	4.5	5	100	75	40	1.1
HPD2200	2200	10	5.2	5	100	-	40	1.1
HPD2200F	2200	10	5.7	5	100	75	40	1.1

Note: Specifications are measured with a 25°C ambient temperature unless stated otherwise. A "-" means a standard recovery device.

Temperature		
T_{STG}	Storage Temperature	-55 to 175°C
T_{OP}	Operating Temperature	-55 to 175°C
T_{JMAX}	Maximum Junction Temperature	175°C

Case Outline and Dimensions



Dimensions in inches [mm]

RoHS COMPLIANT

Note: Specifications subject to change without notice.